

# DN8899/SE/TE/S

Hall IC (Operating Temperature Range  
 $T_{opr} = -40 \text{ to } +100^\circ\text{C}$ ,  
 Operating in Alternative Magnetic Field)

## ■ Overview

The DN8899/SE/TE/S is a combination of a Hall element, amplifier, Schmidt circuit, and stabilized power supply/temperature compensator integrated on an identical chip by using the IC technology. It amplifies Hall element output at the amplifier, converts into a digital signal through the Schmidt circuit, and drives the TTL or MOS IC directly.

## ■ Features

- High sensitivity and low drift
- Stable temperature characteristics due to the additional temperature compensator
- Wide operating supply voltage range ( $V_{CC} = 4.5 \text{ to } 16\text{V}$ )
- Operating in alternative magnetic field
- TTL and MOS ICs directly drivable by output
- Semipermanent service life due to no contact parts
- Small change of the operating flux density against mechanical stress
- Output open collector
- “0” gauss point in the zero cross type hysteresis width

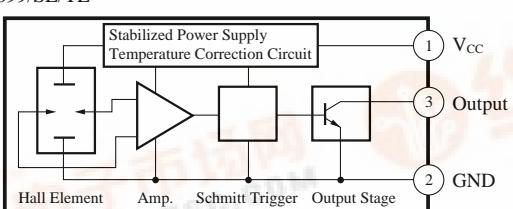
## ■ Applications

- Speed sensors
- Position sensors
- Rotation sensors
- Keyboard switches
- Microswitches

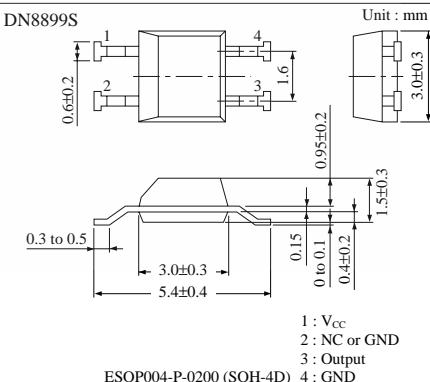
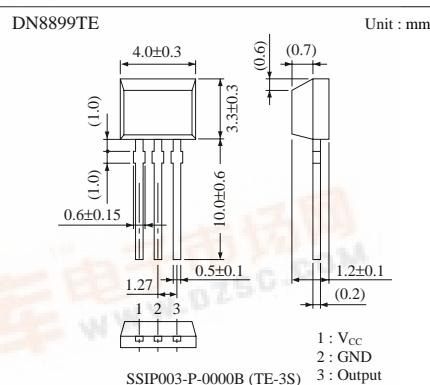
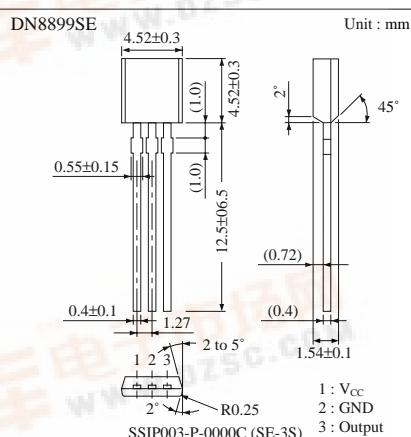
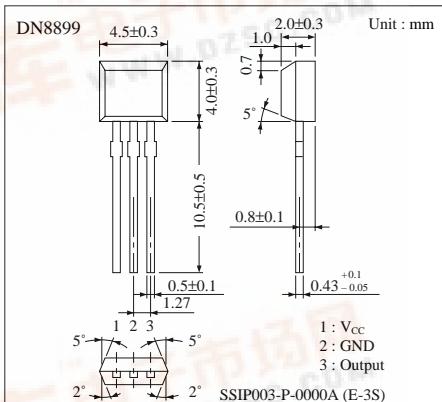
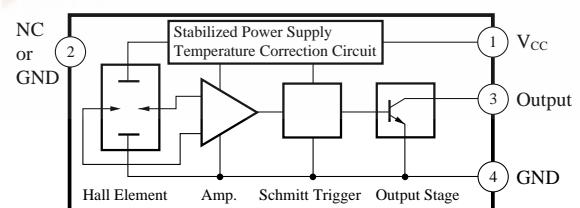
Note) This IC is not suitable for the car electric equipment.

## ■ Block Diagram

### · DN8899/SE/TE



### · DN8899S



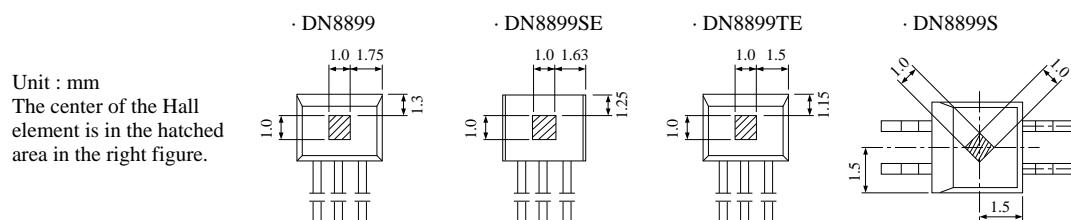
## ■ Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	18	V
Supply current	I <sub>CC</sub>	8	mA
Circuit current	I <sub>O</sub>	20	mA
Power dissipation	P <sub>D</sub>	150	mW
Operating ambient temperature	T <sub>opr</sub>	-40 to +100	°C
Storage temperature	T <sub>stg</sub>	-55 to +125	°C

## ■ Electrical Characteristics (Ta=25°C)

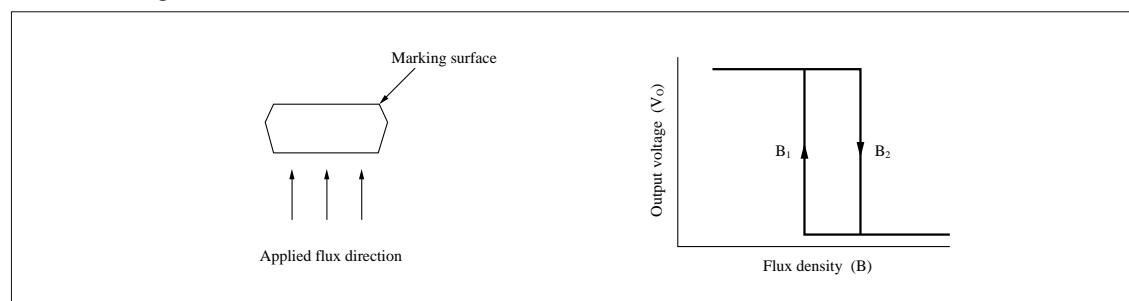
Parameter	Symbol	Condition	min	typ	max	Unit
Operating flux density	B <sub>1</sub> (L→H)	V <sub>CC</sub> =12V	-12	-6	-0.1	mT
	B <sub>2</sub> (H→L)	V <sub>CC</sub> =12V	0.1	6	12	mT
Hysteresis width	BW	V <sub>CC</sub> =12V	7	10	—	mT
Low output voltage	V <sub>OL</sub>	V <sub>CC</sub> =4.5 to 16V, I <sub>O</sub> =12mA, B=12mT	—	—	0.4	V
High output current	I <sub>OH</sub>	V <sub>CC</sub> =4.5 to 16V, V <sub>O</sub> =16V, B=-12mT	—	—	10	μA
Supply current	I <sub>CC</sub>	V <sub>CC</sub> =16V	—	—	6	mA
		V <sub>CC</sub> =4.5V	—	—	5.5	mA

## ■ Hall Element Position



Distance from package surface to sensor (mm)	DN8899	DN8899SE	DN8899TE	DN8899S
	0.7	0.42	0.4	0.65

## ■ Flux-Voltage Conversion Characteristics

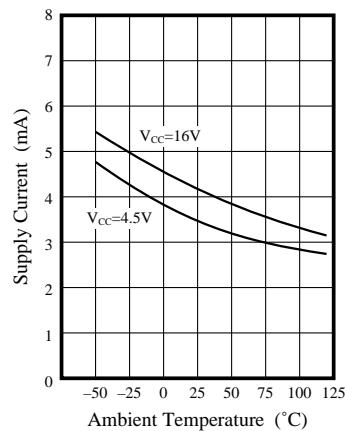


## ■ Supplementary Descriptions

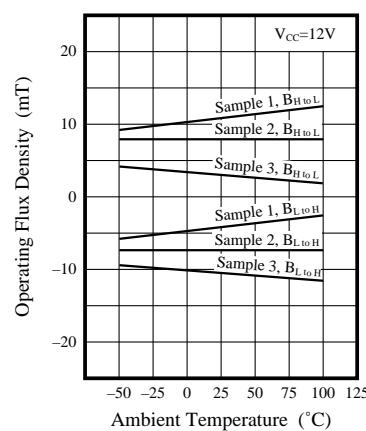
1. Change of the operation magnetic flux density dose not depend on the supply voltage, because the stabilization power supply is built in. (only for the range ;  $V_{CC}=4.5$  to 16V)
2. Change from "H" to "L" level increases the supply current by approx. 1mA.

## ■ Characteristics Curve

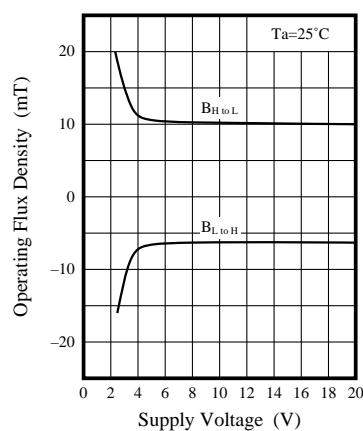
Supply Voltage – Ambient Temperature



Operating Flux Density – Ambient Temperature



Operating Flux Density – Supply Voltage



Output Low Level Voltage – Ambient Temperature

